



DSS2540M

40V NPN LOW V_{CE(sat)} TRANSISTOR

Features

- BV_{CEO} > 40V
- I_C = 500mA High Collector Current
- I_{CM} = 1A Peak Pulse Current
- P_D = 1000mW Power Dissipation
- Low Collector-Emitter Saturation Voltage, V_{CE(sat)}
- 0.60mm² Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DSS3540M
- Totally Lead Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

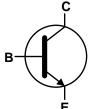
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu.
- Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

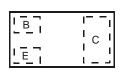




Bottom View



Device Symbol



Top View Device Schematic

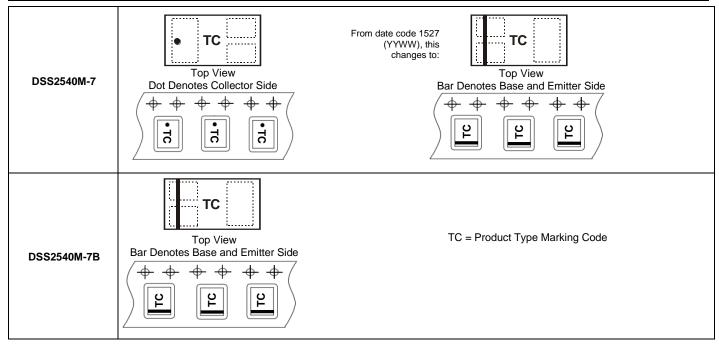
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS2540M-7	TC	7	8mm	3,000
DSS2540M-7B	TC	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current - Continuous	lc	500	mA
Peak Pulse Collector Current	I _{CM}	1	Α
Peak Base Current	I _{BM}	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	400	mW	
Fower Dissipation	(Note 6)	P _D	1000		
Thermal Resistance, Junction to Ambient	(Note 5)	D	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	120		
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

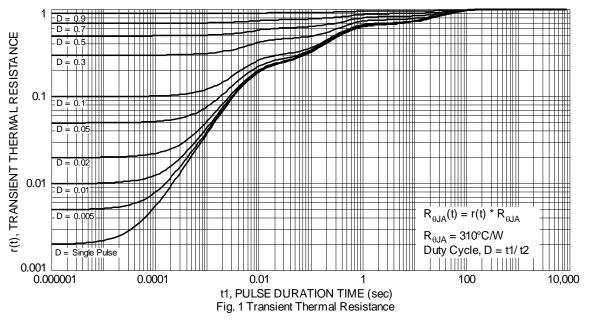
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	В

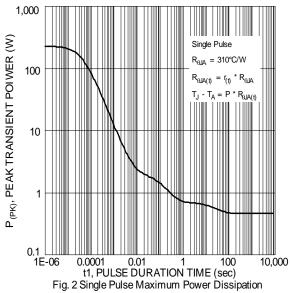
Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





May 2015



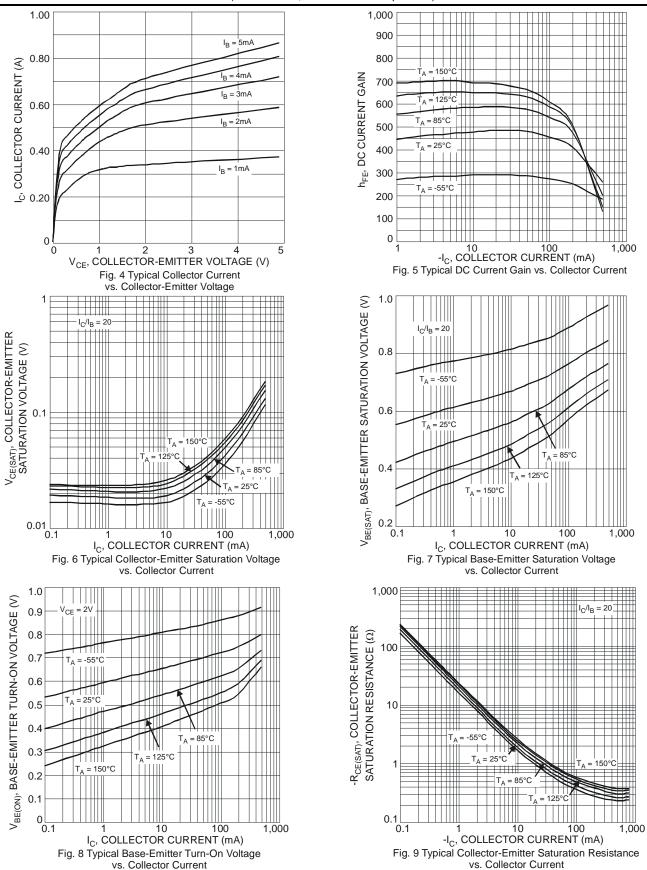
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	40			V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	40	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	$I_E = 100\mu A, I_C = 0$
Collector Cutoff Current	lose	_	_	100	nA	$V_{CB} = 30V, I_{E} = 0$
Collector Cutoff Current	I _{CBO}			50	μΑ	$V_{CB} = 30V, I_E = 0, T_A = +150^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
		200	_	_		$V_{CE} = 2V$, $I_C = 10mA$
DC Current Gain	h_{FE}	150	_	_		$V_{CE} = 2V, I_{C} = 100mA$
		50	_			$V_{CE} = 2V, I_{C} = 500mA$
	VCE(sat)	_	_	50	mV	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$
Collector-Emitter Saturation Voltage		_	_	100		$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
Collector-Emitter Saturation Voltage		_	_	200		$I_C = 200 \text{mA}, I_B = 10 \text{mA}$
			_	250		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	_	500	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.2	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	1.1	V	$V_{CE} = 2V, I_{C} = 100mA$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	_	6	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	250	300		MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



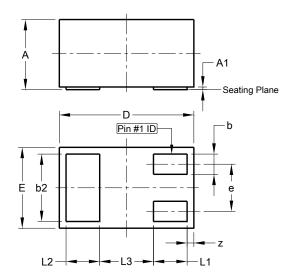
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

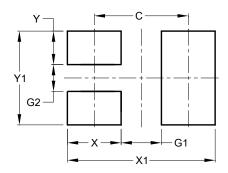
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
ם	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	-		0.35	
ľ	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
Z	0.02	0.08	0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.70		
G1	0.30		
G2	0.20		
Х	0.40		
X1	1.10		
Y	0.25		
Y1	0.70		



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